

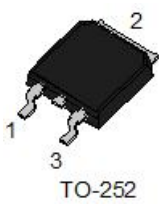
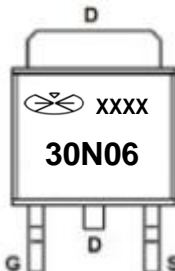
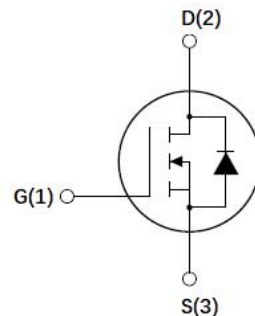


30N06

N-Channel Mode Power MOSFET

<p>Features</p> <ul style="list-style-type: none"> • Hard density cell design for ultra low $R_{DS(ON)}$ • Low gate charge 	<p>Application</p> <ul style="list-style-type: none"> • Hard switched and high frequency circuits • Uninterruptible power supply
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Package

Package Marking and Ordering Information

Product ID	PACK	Qty (pcs)
30N06	TO-252	2500

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	30	A
I_{DM}	Pulsed Drain Current	80	A
P_D	Power Dissipation	1.25	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to 150	
$R\theta_{JA}$	Thermal Resistance From Junction To Ambient	100	°C/W
$R\theta_{JC}$	Thermal Resistance From Junction To Case	2.6	°C/W



**30N06****N-Channel Mode Power MOSFET****MOSFET ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)**

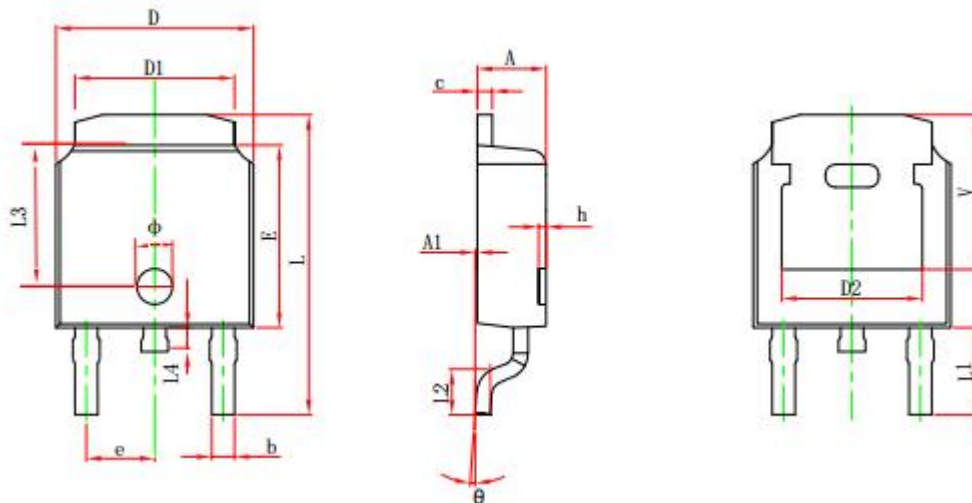
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Off characteristics						
Drain-Source breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			100	nA
Gate-body leakage current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
On characteristics						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1		2.1	V
Non-triggering gate voltage	$R_{DS(on)}$	$V_{GS}=10V, I_D=1.0A$		12	15	m Ω
		$V_{GS}=4.5V, I_D=1.0A$		17	24	m Ω
Drain-Source Diode Characteristics						
Drain-Source diode forward Voltage	VSD	$V_{GS}=0V, I_S=10A$			1.2	V
Continuous drain-source diode forward current	I_S				30	A



30N06

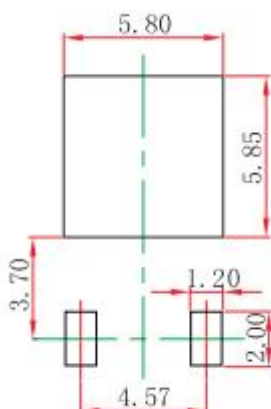
N-Channel Mode Power MOSFET

TO-252-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	4.460 REF.		0.1756 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

TO-252-2L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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